1. Scope :

This specification applies to N/P silicon zener diode chips,
Device NO. SD-20960GL

2. Structure :

2-1. Planar type : N/P Diode
2-2. Electrodes :
Top side : Gold pad.
Back side : Gold layer.

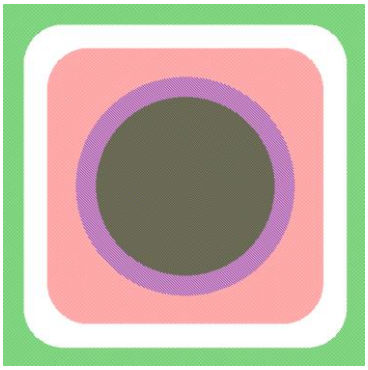
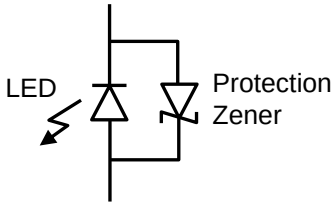
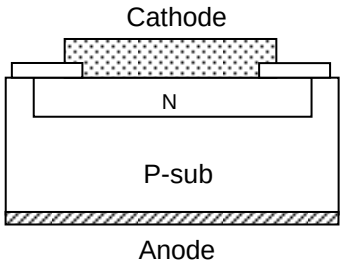
3. Size :

3-1. ※1Chip size : 9.06 mils x 9.06 mils (0.230 mm x 0.230 mm).
3-2. Chip thickness : 7.1 ± 1.0 mils (0.180 ± 0.0254 mm).
3-3. Active area : 6.7 mils x 6.7 mils (0.170 mm x 0.170 mm).
3-4. ※2Bonding pad : ϕ 5.1 mils (ϕ 0.130 mm).
3-5. Pattern drawing : Refer to the attached drawing.

※1Including scribing line. The chip size is about $(0.210\pm0.020)^2 mm^2$ after dicing.
※2 The bonding pad dimension is $(0.130\pm0.0010)^2 mm^2$.

4. Electrical characteristics (Ta = 25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Leakage Current	I_R	V_R=4V Ee=0mW/cm²			100	nA
Zener Voltage	Vz	I_Z=5mA Ee=0mW/cm²	5.7		6.7	V
Forward Voltage	Vf	I_F=20mA Ee=0mW/cm²			1.2	V



Equivalent Circuit